# Contents

## 1. Introduction

1.1 A Survey of Semiconductors .................................................. 2  
1.1.1 Elemental Semiconductors ........................................ 2  
1.1.2 Binary Compounds ..................................................... 2  
1.1.3 Oxides ........................................................................... 3  
1.1.4 Layered Semiconductors .............................................. 3  
1.1.5 Organic Semiconductors .............................................. 4  
1.1.6 Magnetic Semiconductors .......................................... 4  
1.1.7 Other Miscellaneous Semiconductors ............................ 4  
1.2 Growth Techniques ........................................................... 5  
1.2.1 Czochralski Method ................................................... 5  
1.2.2 Bridgman Method ....................................................... 6  
1.2.3 Chemical Vapor Deposition ....................................... 7  
1.2.4 Molecular Beam Epitaxy .......................................... 8  
1.2.5 Fabrication of Self-Organized Quantum Dots  
by the Stranski–Krastanow Growth Method ...................... 11  
1.2.6 Liquid Phase Epitaxy .............................................. 13  
Summary .................................................................................. 14  
Periodic Table of “Semiconductor-Forming” Elements ........ 15

## 2. Electronic Band Structures

2.1 Quantum Mechanics .......................................................... 18  
2.2 Translational Symmetry and Brillouin Zones ......................... 20  
2.3 A Pedestrian’s Guide to Group Theory ................................ 25  
2.3.1 Definitions and Notations ......................................... 25  
2.3.2 Symmetry Operations of the Diamond  
and Zinc-Blende Structures ............................................ 30  
2.3.3 Representations and Character Tables .......................... 32  
2.3.4 Some Applications of Character Tables ....................... 40  
2.4 Empty Lattice or Nearly Free Electron Energy Bands .......... 48  
2.4.1 Nearly Free Electron Band Structure  
in a Zinc-Blende Crystal .................................................. 48  
2.4.2 Nearly Free Electron Energy Bands in Diamond Crystals 52  
2.5 Band Structure Calculations by Pseudopotential Methods .... 58  
2.5.1 Pseudopotential Form Factors  
in Zinc-Blende- and Diamond-Type Semiconductors .......... 61  
2.5.2 Empirical and Self-Consistent Pseudopotential Methods 66
2.6 The \( k \cdot p \) Method of Band-Structure Calculations ............... 68
  2.6.1 Effective Mass of a Nondegenerate Band
    Using the \( k \cdot p \) Method .................................. 69
  2.6.2 Band Dispersion near a Degenerate Extremum:
    Top Valence Bands in Diamond- and Zinc-Blende-Type Semiconductors ............. 71
2.7 Tight-Binding or LCAO Approach to the Band Structure
    of Semiconductors ........................................ 83
  2.7.1 Molecular Orbitals and Overlap Parameters .................. 83
  2.7.2 Band Structure of Group-IV Elements
    by the Tight-Binding Method ................................ 87
  2.7.3 Overlap Parameters and Nearest-Neighbor Distances .......... 94
Problems ..................................................... 96
Summary .................................................... 105

3. Vibrational Properties of Semiconductors,
   and Electron–Phonon Interactions .......................... 107
  3.1 Phonon Dispersion Curves of Semiconductors ................. 110
  3.2 Models for Calculating Phonon Dispersion Curves
    of Semiconductors ........................................ 114
    3.2.1 Force Constant Models ................................ 114
    3.2.2 Shell Model ........................................... 114
    3.2.3 Bond Models ........................................... 115
    3.2.4 Bond Charge Models ................................... 117
  3.3 Electron–Phonon Interactions ................................ 121
    3.3.1 Strain Tensor and Deformation Potentials ................. 122
    3.3.2 Electron–Acoustic-Phonon Interaction
      at Degenerate Bands ...................................... 127
    3.3.3 Piezoelectric Electron–Acoustic-Phonon Interaction .... 130
    3.3.4 Electron–Optical-Phonon
      Deformation Potential Interactions ....................... 131
    3.3.5 Fröhlich Interaction ................................... 133
    3.3.6 Interaction Between Electrons and Large-Wavevector
      Phonons: Intervalley Electron–Phonon Interaction ....... 135
Problems ..................................................... 137
Summary .................................................... 158

4. Electronic Properties of Defects .............................. 159
  4.1 Classification of Defects ..................................... 160
  4.2 Shallow or Hydrogenic Impurities ............................. 161
    4.2.1 Effective Mass Approximation .......................... 162
    4.2.2 Hydrogenic or Shallow Donors ......................... 166
    4.2.3 Donors Associated with Anisotropic Conduction Bands 171
    4.2.4 Acceptor Levels in Diamond- and Zinc-Blende-Type Semiconductors ............ 174
  4.3 Deep Centers ............................................. 180
4.3.1 Green’s Function Method for Calculating Defect Energy Levels .......... 183
4.3.2 An Application of the Green’s Function Method: Linear Combination of Atomic Orbitals .......... 188
4.3.3 Another Application of the Green’s Function Method: Nitrogen in GaP and GaAsP Alloys .......... 192
4.3.4 Final Note on Deep Centers .......... 197
Problems ........................................ 198
Summary ........................................ 202

5. Electrical Transport ........................................ 203
5.1 Quasi-Classical Approach ........................................ 203
5.2 Carrier Mobility for a Nondegenerate Electron Gas ........................................ 206
5.2.1 Relaxation Time Approximation ........................................ 206
5.2.2 Nondegenerate Electron Gas in a Parabolic Band ........................................ 207
5.2.3 Dependence of Scattering and Relaxation Times on Electron Energy ........................................ 208
5.2.4 Momentum Relaxation Times ........................................ 209
5.2.5 Temperature Dependence of Mobilities ........................................ 220
5.3 Modulation Doping ........................................ 223
5.4 High-Field Transport and Hot Carrier Effects ........................................ 225
5.4.1 Velocity Saturation ........................................ 227
5.4.2 Negative Differential Resistance ........................................ 228
5.4.3 Gunn Effect ........................................ 230
5.5 Magneto-Transport and the Hall Effect ........................................ 232
5.5.1 Magneto-Conductivity Tensor ........................................ 232
5.5.2 Hall Effect ........................................ 234
5.5.3 Hall Coefficient for Thin Film Samples (van der Pauw Method) ........................................ 235
5.5.4 Hall Effect for a Distribution of Electron Energies ........................................ 236
Problems ........................................ 237
Summary ........................................ 241

6. Optical Properties I ........................................ 243
6.1 Macroscopic Electrodynamics ........................................ 244
6.1.1 Digression: Units for the Frequency of Electromagnetic Waves ........................................ 247
6.1.2 Experimental Determination of Optical Functions ........................................ 247
6.1.3 Kramers–Kronig Relations ........................................ 250
6.2 The Dielectric Function ........................................ 253
6.2.1 Experimental Results ........................................ 253
6.2.2 Microscopic Theory of the Dielectric Function ........................................ 254
6.2.3 Joint Density of States and Van Hove Singularities ........................................ 261
6.2.4 Van Hove Singularities in $\varepsilon_i$ ........................................ 262
6.2.5 Direct Absorption Edges ........................................ 268
6.2.6 Indirect Absorption Edges ........................................ 269
6.2.7 “Forbidden” Direct Absorption Edges 273

6.3 Excitons 276

6.3.1 Exciton Effect at \( M_0 \) Critical Points 279
6.3.2 Absorption Spectra of Excitons 282
6.3.3 Exciton Effect at \( M_1 \) Critical Points or Hyperbolic Excitons 288
6.3.4 Exciton Effect at \( M_3 \) Critical Points 291

6.4 Phonon-Polaritons and Lattice Absorption 292

6.4.1 Phonon-Polaritons 295
6.4.2 Lattice Absorption and Reflection 298
6.4.3 Multiphonon Lattice Absorption 299
6.4.4 Dynamic Effective Ionic Charges in Heteropolar Semiconductors 303

6.5 Absorption Associated with Extrinsic Electrons 305

6.5.1 Free-Carrier Absorption in Doped Semiconductors 306
6.5.2 Absorption by Carriers Bound to Shallow Donors and Acceptors 311

6.6 Modulation Spectroscopy 315

6.6.1 Frequency Modulated Reflectance and Thermoreflectance 319
6.6.2 Piezoreflectance 321
6.6.3 Electrorefelectance (Franz–Keldysh Effect) 322
6.6.4 Photoreflectance 329
6.6.5 Reflectance Difference Spectroscopy 332

6.7 Addendum (Third Edition): Dielectric Function 333

Problems 342
Summary 343

7. Optical Properties II 345

7.1 Emission Spectroscopies 345

7.1.1 Band-to-Band Transitions 351
7.1.2 Free-to-Bound Transitions 354
7.1.3 Donor–Acceptor Pair Transitions 356
7.1.4 Excitons and Bound Excitons 362
7.1.5 Luminescence Excitation Spectroscopy 369

7.2 Light Scattering Spectroscopies 375

7.2.1 Macroscopic Theory of Inelastic Light Scattering by Phonons 375
7.2.2 Raman Tensor and Selection Rules 378
7.2.3 Experimental Determination of Raman Spectra 385
7.2.4 Microscopic Theory of Raman Scattering 394
7.2.5 A Detour into the World of Feynman Diagrams 395
7.2.6 Brillouin Scattering 398
7.2.7 Experimental Determination of Brillouin Spectra 400
7.2.8 Resonant Raman and Brillouin Scattering 401

Problems 422
Summary 426
8. Photoelectron Spectroscopy

8.1 Photoemission

8.1.1 Angle-Integrated Photoelectron Spectra of the Valence Bands

8.1.2 Angle-Resolved Photoelectron Spectra of the Valence Bands

8.1.3 Core Levels

8.2 Inverse Photoemission

8.3 Surface Effects

8.3.1 Surface States and Surface Reconstruction

8.3.2 Surface Energy Bands

8.3.3 Fermi Level Pinning and Space Charge Layers

Problems

Summary

9. Effect of Quantum Confinement on Electrons and Phonons in Semiconductors

9.1 Quantum Confinement and Density of States

9.2 Quantum Confinement of Electrons and Holes

9.2.1 Semiconductor Materials for Quantum Wells and Superlattices

9.2.2 Classification of Multiple Quantum Wells and Superlattices

9.2.3 Confinement of Energy Levels of Electrons and Holes

9.2.4 Some Experimental Results

9.3 Phonons in Superlattices

9.3.1 Phonons in Superlattices: Folded Acoustic and Confined Optic Modes

9.3.2 Folded Acoustic Modes: Macroscopic Treatment

9.3.3 Confined Optical Modes: Macroscopic Treatment

9.3.4 Electrostatic Effects in Polar Crystals: Interface Modes

9.4 Raman Spectra of Phonons in Semiconductor Superlattices

9.4.1 Raman Scattering by Folded Acoustic Phonons

9.4.2 Raman Scattering by Confined Optical Phonons

9.4.3 Raman Scattering by Interface Modes

9.4.4 Macroscopic Models of Electron–LO Phonon (Frohlich) Interaction in Multiple Quantum Wells

9.5 Electrical Transport: Resonant Tunneling

9.5.1 Resonant Tunneling Through a Double-Barrier Quantum Well

9.5.2 I–V Characteristics of Resonant Tunneling Devices

9.6 Quantum Hall Effects in Two-Dimensional Electron Gases

9.6.1 Landau Theory of Diamagnetism in a Three-Dimensional Free Electron Gas

9.6.2 Magneto-Conductivity of a Two-Dimensional Electron Gas: Filling Factor
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